

MICRO ELECTRO

NPN
SILICON
TRANSISTOR

DESCRIPTION

2N3414 is NPN silicon transistor designed for general purpose AF medium power applications.

TO-92



ECB

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	V _{CEO}	25V
Collector-Emitter Voltage	V _{CBO}	25V
Emitter-Base Voltage	V _{EBO}	5V
Collector Current	I _C	500mA
Operating & Storage Junction Temperature	T _j , T _{stg}	-55 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS

(T_a=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BV _{CBO}	25		V	I _C =100μA I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	25		V	I _C =10mA I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	5		V	I _E =10μA I _C =0
Collector Cutoff Current	I _{CBO}		100	nA	V _{CB} =50V I _E =0
Emitter Cutoff Current	I _{EBO}		100	nA	V _{EB} =5V I _C =0
D.C. Current Gain	h _{FE}	75	225		I _C =2mA V _{CE} =4.5V
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.3	V	I _C =50mA I _B =3mA
Base-Emitter Saturation Voltage	V _{BE(sat)}		0.85	V	I _C =50mA I _B =3mA
Small Signal Current Gain	h _{fe}	300	TYP		I _C =1mA V _{CE} =10V f=1KHz



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